## 2SK1070

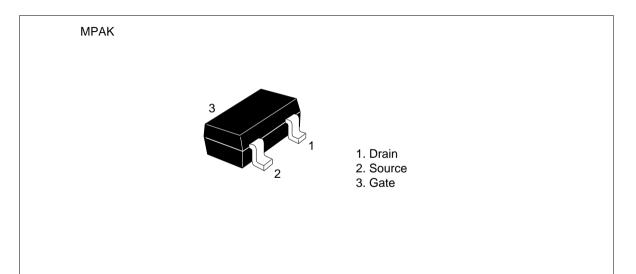
## Silicon N-Channel Junction FET

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#### Application

Low frequency / High frequency amplifier

#### Outline





## 2SK1070

## **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

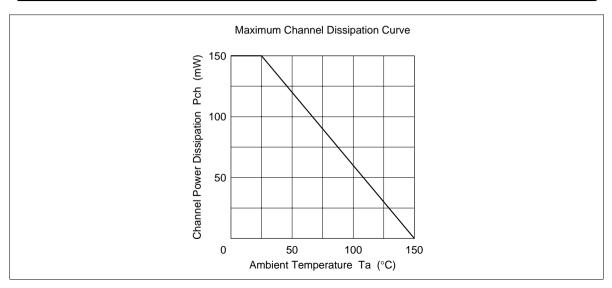
Item	Symbol	Ratings	Unit	
Gate to drain voltage	$V_{GDO}$	-22	V	
Gate to source voltage	V <sub>GSO</sub>	-22	V	
Drain current	Ι <sub>D</sub>	50	mA	
Gate current	Ι <sub>G</sub>	10	mA	
Channel power dissipation	Pch	150	mW	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

### **Electrical Characteristics** (Ta = 25°C)

ltem		Symbol	Min	Тур	Max	Unit	Test conditions	
Gate cutoff	current	I <sub>GSS</sub>	_	_	-10	nA	$V_{GS} = -15 V, V_{DS} = 0$	
Gate to sou voltage	rce breakdown	$V_{(\text{BR})\text{GSS}}$	-22	_		V	$I_{g} = -10 \ \mu A, \ V_{DS} = 0$	
Drain currer	nt	I_ss <sup>+1</sup>	6	—	40	mA	$V_{DS} = 5 \text{ V}, \text{ V}_{GS} = 0, \text{ Pulse test}$	
Gate to sou	rce cutoff voltag	ge V <sub>GS(off)</sub>	0	—	-2.5	V	$V_{\text{DS}}$ = 5 V, $I_{\text{D}}$ = 10 $\mu$ A	
Forward tra	nsfer admittanc	e y <sub>fs</sub>	20	30	—	mS	$V_{DS} = 5 \text{ V}, V_{GS} = 0, f = 1 \text{ kHz}$	
Input capac	itance	Ciss	—	9	—	pF	$V_{DS} = 5 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	
Note: 1. The 2SK1070 is grouped by I <sub>DSS</sub> as follows.								
Grade	В	С	D		E			
Mark	PIB	PIC	PID		PIE			
I <sub>DSS</sub>	6 to 14	12 to 22	18 to 3	0	27 to 40			

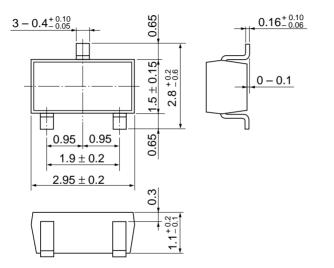
See characteristic curves of 2SK435.

## 2SK1070



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Unit: mm



Hitachi Code	MPAK
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.011 g

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Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109 NorthAmerica URL http:semiconductor.hitachi.com/ http://www.hitachi-eu.com/hel/ecg Europe http://www.has.hitachi.com.sg/grp3/sicd/index.htm http://www.hitachi.com.tw/E/Product/SICD\_Frame.htm Asia (Singapore) Asia (Taiwan) Asia (HongKong) http://www.hitachi.com.hk/eng/bo/grp3/index.htm http://www.hitachi.co.jp/Sicd/indx.htm Japan For further information write to: Hitachi Semiconductor Hitachi Europe GmbH Hitachi Asia Pte. Ltd. (America) Inc. Electronic components Group 16 Collyer Quay #20-00 179 East Tasman Drive, Dornacher Stra§e 3 Hitachi Tower San Jose,CA 95134 D-85622 Feldkirchen, Munich Singapore 049318 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Germany Tel: 535-2100 Tel: <49> (89) 9 9180-0 Fax: 535-1533 Fax: <49> (89) 9 29 30 00

 Fax: <49> (89) 9 29 30 00
 Hita

 Hitachi Europe Ltd.
 Hita

 Electronic Components Group.
 Taip

 Whitebrook Park
 3F,

 Lower Cookham Road
 Tun

 Maidenhead
 Tel:

 Berkshire SL6 8YA, United Kingdom
 Fax

 Tel: <44> (1628) 585000

 Fax: <44> (1628) 778322

Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

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Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281 Telex: 40815 HITEC HX

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